

# **Ultra CSP (Wafer Level Packaging)**

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# Ultra CSP

ASE Research & Development

ASE, Inc.

1



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## Content

- ◆ Introduction
- ◆ Process Overview
- ◆ Process Characterization
- ◆ Package Menu
- ◆ Performance
- ◆ Design Rule
- ◆ Qualification Plan
- ◆ Capacity & Cycle Time
- ◆ Competitive Advantage
- ◆ Summary

# Introduction



## - What is Ultra CSP?

- **Wafer-level Packaging**

Wafer-level packaging has sets of area array bonding pads on the wafer or forms the sets of area array bonding pads by means of redistribution of the peripheral bonding pads of each die in the wafer fabrication process. Moreover, the interconnect medium on the pad is built via various ways to enable direct chip attach.

- **Ultra CSP**

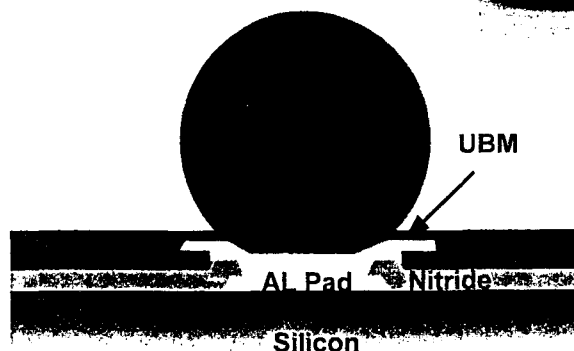
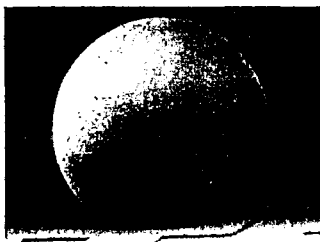
Ultra CSP is one of wafer-level packaging, which allow direct ball drop process in wafer form to establish its interconnection medium for direct board assembly. It is a patented process by *Flip Chip Technologies*.

3

# Introduction



## - Illustration of Ultra CSP



38

4

# Introduction



## - Features

- Real chip size (smallest, thinnest and lightest)
- High density interconnection
- High-speed data processing
- Batch process- assembly processed in wafer form (cost competitive, even better for 12 inch wafer)
- Limitation of higher pin-count
- Lack of package standardization

Ideal package for low pin-count application!

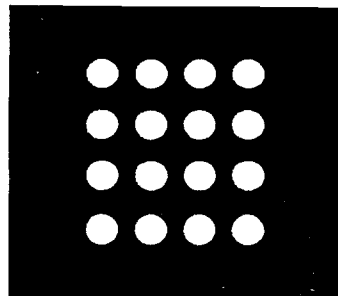
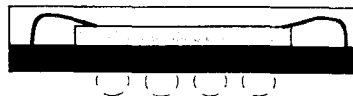
5

# Introduction

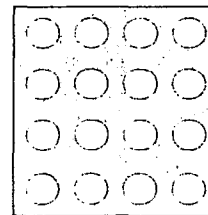
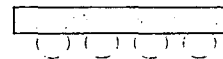


## - Ultra CSP v.s. WB CSP

### WB CSP



### Ultra CSP™



“Package size” & “Electrical path” shrink.



39

6

# Introduction



- Ultra CSP v.s. Flip Chip CSP

Flip Chip (solder bumps)		Ultra CSP™ (solder balls)
		
4 ~ 3600	I/O count	4 ~ 100
>150 μm	Min. I/O pitch	0.5 mm
100 μm typical	Solder diameter	300-500 μm
100 μm typical	Solder Height	220 ~ 400 μm
High accuracy	SMT Equipment	Standard
0.4 ~ 0.75 mm	Package Height	0.6 ~ 1.1 mm
Yes	Underfill	No

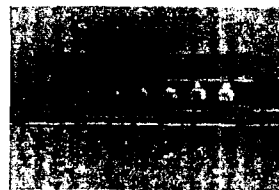
7

# Introduction



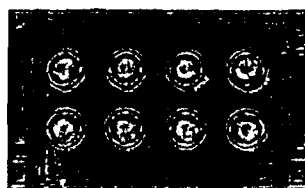
- Applications

- Application
  - Memory (EEPROM, Flash, DRAM & SRAM)
  - Integrated Passives
  - Analog Device (RF)
  - Digital Signal Processor (DSP)
  - Power & Voltage Regulator
  - Power Amplifier



Casio Camera Watch

- Products
  - Cell phone
  - Portable consumer products (PDA, Digital camera...)
  - System boards



Atmel EEPROM

Photos provided by Pristmark

8

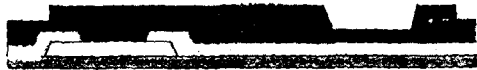
# Process Overview



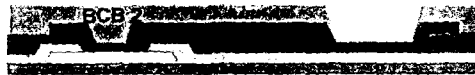
## - Process Flow



Apply first-layer polymer onto wafer



Sputter UBM and form trace and pad



Apply second-layer polymer onto wafer

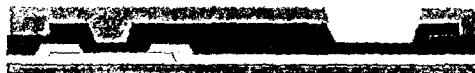
# Process Overview



## - Process Flow (Cont'd)



Backside Grinding  
Backside Laser Marking



Solder Ball Attach  
Reflow  
Cleaning



Wafer Mount  
Wafer Saw (Singulation)



or



Pick & Place  
FVI  
Packing (Tape & Reel / Waffle pack  
Wafer box)

# Process Characterization



## - Process Capability and Limitation

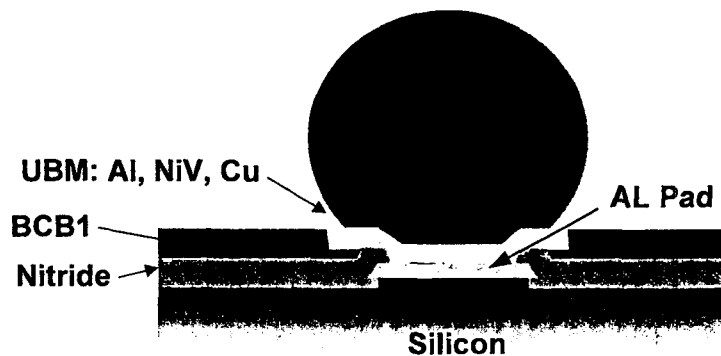
- **Redistribution**                      Standard pitch 50um (Line/Space=38/12um)  
   Fine Pitch        37um (Line/Space=25/12um)
- **Laser Marking**                      0.3mm (Font Height) x 0.2mm (Font Pitch)
- **Wafer Grinding**                      12mil min.
- **Ball Mounting**                      Sn/Pb=63/37    0.3 / 0.5mm Ball Pitch
- **Wafer Sawing**                      80um min. Scribe Line
- **Packing**                                0.5x0.5mm min. for Waffle Pack  
   1.0x1.0mm min. for Tape and Reel

11

# Package Menu



## - Structure 1: Re-passivation



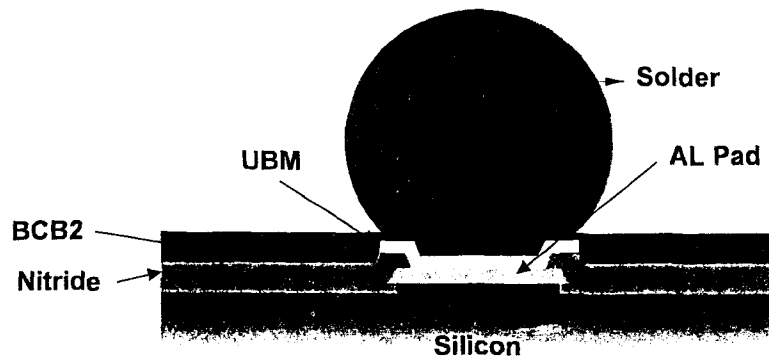
- Note:**
1. Not in scale
  2. Nitride 1um, UBM 2um, BCB 3um
  3. BCB: Benzocyclobutene
  4. BCB: dielectric, planarizing & stress buffer

42

12

# Package Menu

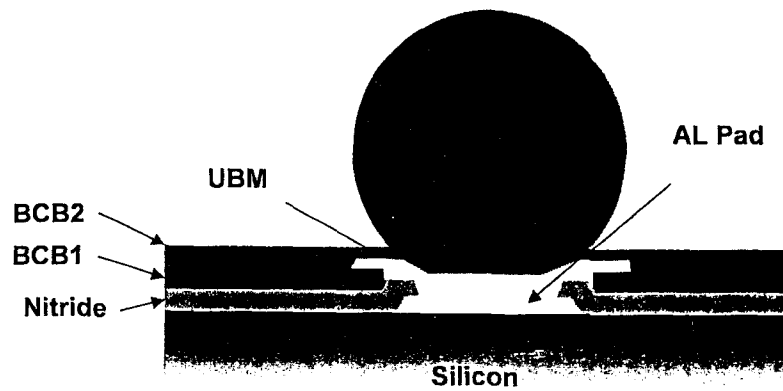
- Structure 2: One-layer BCB



13

# Package Menu

- Structure 3: Two-layer BCB



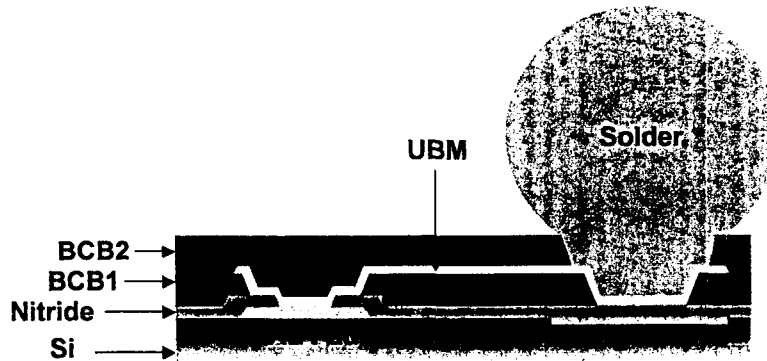
43

14



# Package Menu

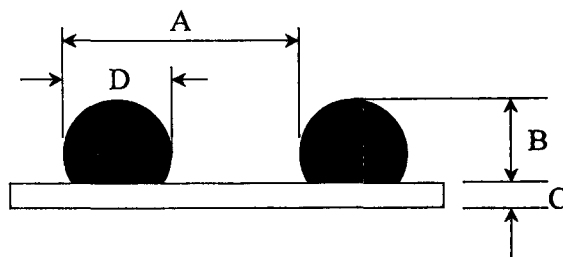
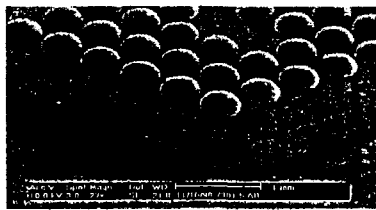
## -Structure 4: Redistribution



15

# Package Menu

## - Critical Geometric Dimensions



Pitch (mm)	Ball Size (mm)	Ball Height (mm)	Die Thick. (mm)	Ball Diameter (mm)
A		B	C	D
0.50	0.30	0.22	0.33 ~ 0.73	0.32
0.50	0.35	0.28	0.33 ~ 0.73	0.38
0.65	0.35	0.28	0.33 ~ 0.73	0.38
0.75	0.50	0.38	0.33 ~ 0.73	0.54
0.80	0.50	0.38	0.33 ~ 0.73	0.54

\*Total Height: 0.6~1.1mm

# Package Menu



- Experience (Processed Devices)

<b>Wafer size (inch)</b>	<b>6 ~ 8</b>
<b>Die size (mm)</b>	<b>1.45x1.45 ~ 6.9x6.45</b>
<b>Ball pitch (mm)</b>	<b>0.5, 0.75 and 0.8</b>
<b>Ball size (mm)</b>	<b>0.3 and 0.5</b>
<b>Ball count</b>	<b>8~ 98</b>

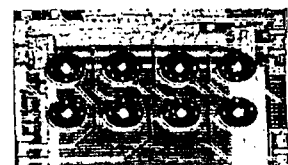
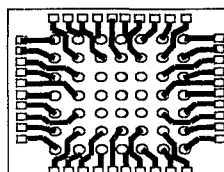
17

# Design Rule



- Basic Wafer Request

- **Passivation type** Nitride or Oxynitride, but not Polyimide.
- **Scribe Line Width** BCB inside die passivation step is preferable.  
(Min. scribe line for die saw ability is 80 um)
- **Inking** No inked wafer is required
- **Min. thickness** 6 inches wafer : 18~40 mils  
8 inches wafer : 22~40 mils



45

18

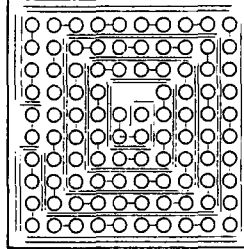
# Qualification Plan



## - Test Vehicles

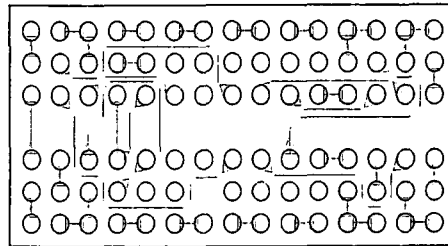
### Ultra CSP™ 50

0.50 mm pitch  
 0.30 mm ball  
 10 x 10 array  
 Die Size : 6.9x6.45mm  
 Max. DMP = 3.18  
 No. I/O = 98



### Ultra CSP™ 80

0.80 mm pitch  
 0.50 mm ball  
 7 x 15 array  
 Die Size : 13.0x6.50mm  
 Max. DMP = 6.10  
 No. I/O = 90



# Qualification Plan



## - Package Level Tests

Tests Methods	S.S.	Test Conditions	
<b>MSL test</b>			
- MSL 1	270	85 °C /85%RH/168hrs + IRx3 (240°C)	
- MSL 2	270	85 °C /60%RH /168hrs+ IRx3 (240°C)	
- MSL 3	270	30 °C /60%RH /192hrs+ IRx3 (240°C)	
<b>Reliability test</b>			
- TCT	45	-55 ~ 125 °C	1000 cycles
- HAST	45	130°C /85%RH /33.6 psia	100 hrs
- THT	45	85 °C /85%RH	1000 hrs
- HTST	45	150 °C	1000 hrs

# Qualification Plan



## - Board Level Tests

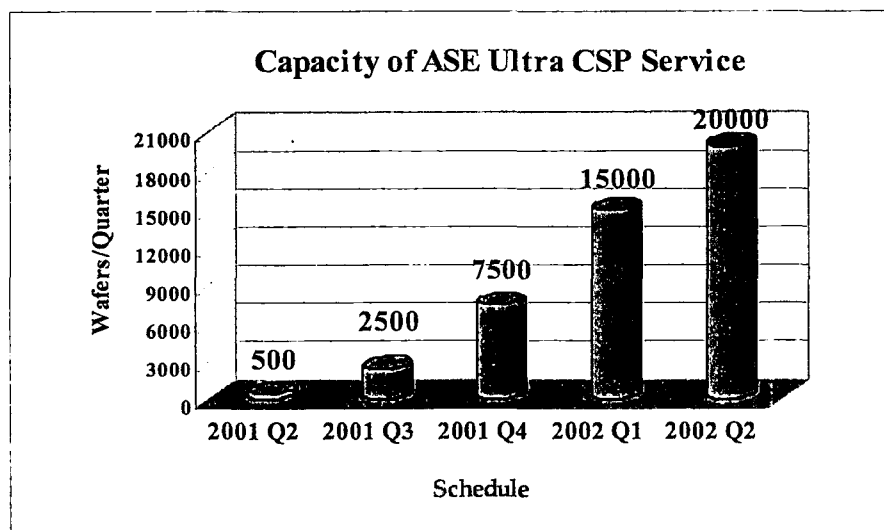
Tests Methods	S.S.	Test Conditions	
1. TCT	32	-40 °C ~ 125 °C	1000 cycles
2. Bending Test	10	1 mm deflection @ 1Hz	
3. Drop Test	10	1 meter height	

21

# Capacity & Cycle Time



## - Capacity



Note: Combined capacity of 6" and 8" wafers based on 3K dice/ Wafer

47

22

# Capacity & Cycle Time



- Cycle Time

	Mask		Ball Mount Tool		Process	
	Design	MFG	Auto	Manual	1st Si	Production
			Design+MFG	Design+MFG		
<b>Bumping</b>	2	5	NA	NA	10	6
<b>REP (1 BCB)</b>	3	5	NA	NA	12	7
<b>RDL (2 BCB)</b>	15	5	NA	NA	15	8
<b>UCSP (1 BCB)</b>	3	5	25	7	15	9
<b>UCSP (2 BCB)</b>	15	5	25	7	17	10

Units: working day

23

# Roadmap



- Ultra CSP Technology Roadmap

**Eutectic solder ball**

**Ready**

**Lead-free solder ball**

**Mar. '02**

# Milestone



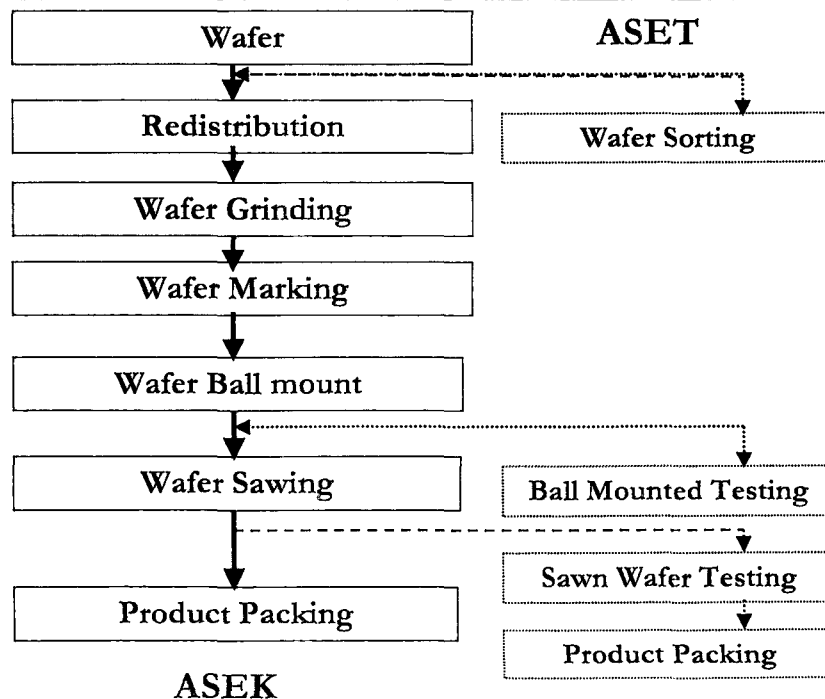
- Ultra CSP Readiness

- |                               |          |
|-------------------------------|----------|
| • Project master plan         | Finished |
| • Machine survey and delivery | Finished |
| • Prototype                   | Ready    |
| • Internal qualification      | Finished |
| • Pre-production              | Q4 2001  |

# Competitive Advantage



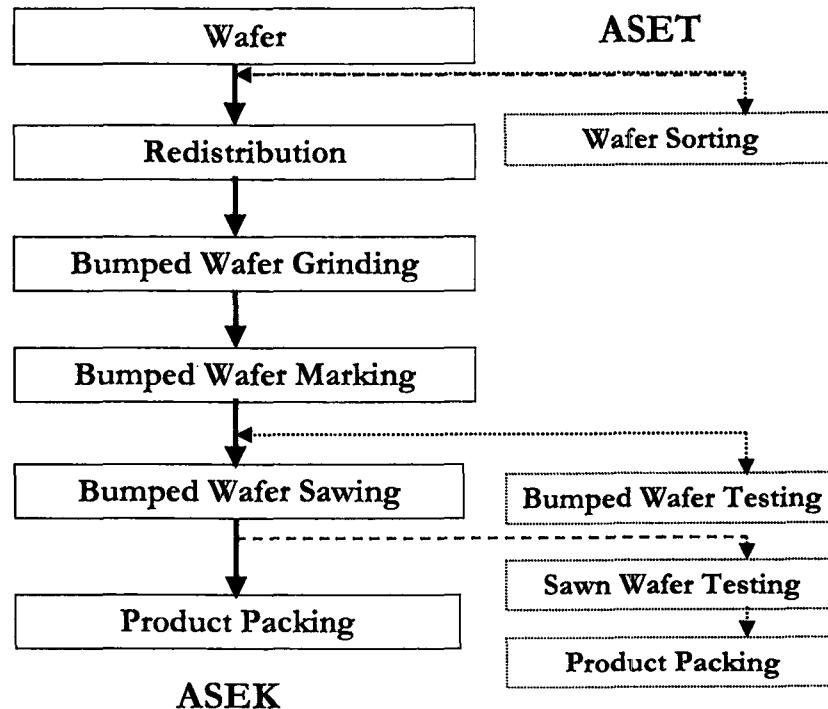
- ASE edge: Total Solution for Ultra CSP



# Competitive Advantage



- ASE edge: Total Solution for WLCSP



27

## Summary



- Ideal package solution for low pin-count devices. Success has been found in memory and integrated passive devices.
- The application is being extended to power and RF module and DSP.
- The combined service of wafer BCB re-passivation process and backend assembly process in ASE, make it more reliable in the aspects of both quality and time-to-market. The said service is available for both 6" and 8" wafers.
- Moreover, ASE provides a total turn-key solution which includes wafer sorting, re-passivation, backend assembly and final test.
- However, the service can be flexible and limited to backend only, including backside grinding, marking, singulation and pick & place.